



## Description

### JMG N-channel Enhancement Mode Power MOSFET

#### Features

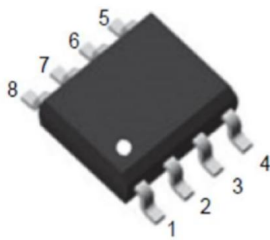
- 100V,7A  
 $R_{DS(ON)} < 140m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 179m\Omega @ V_{GS} = 4.5V$
- Advanced Split Gate Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- Lead free product is acquired

#### Application

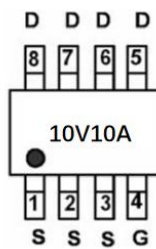
- Load Switch
- PWM Application
- Power management



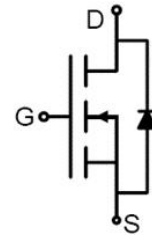
*100% UIS TESTED!*  
*100% ΔVds TESTED!*



SOP-8 top view



Marking and pin Assignment



Schematic Diagram

## Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
10V10A	JMGP10V10A	TAPING	SOP-8	13inch	4000	48000

## Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V <sub>DSS</sub>	Drain-Source Voltage	100	V
V <sub>GSS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	T <sub>A</sub> = 25°C	7
		T <sub>A</sub> = 100°C	4.5
I <sub>DM</sub>	Pulsed Drain Current <sup>note1</sup>	28	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy <sup>note2</sup>	1.6	mJ
P <sub>D</sub>	Power Dissipation	11.7	W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	10.7	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C



## Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

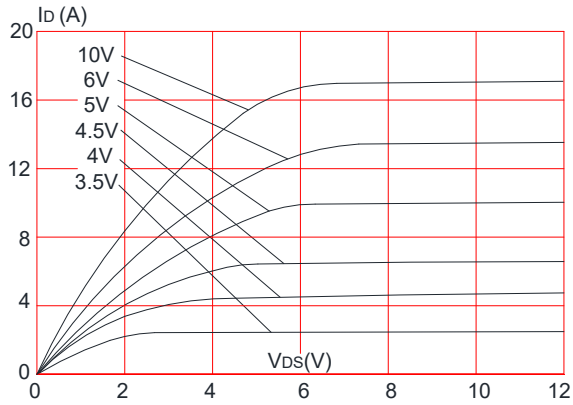
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.7	2.5	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A	-	108	140	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	-	128	179	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	-	150	-	pF
C <sub>oss</sub>	Output Capacitance		-	34	-	pF
C <sub>riss</sub>	Reverse Transfer Capacitance		-	6	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =50V, I <sub>D</sub> =5A, V <sub>GS</sub> =10V	-	4.3	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	1.5	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	1.1	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =50V, I <sub>D</sub> =5A, R <sub>GEN</sub> =2Ω, V <sub>GS</sub> =10V	-	14.7	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	3.5	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	20.9	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	2.7	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	7	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	28	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =7A	-	-	1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =5A, di/dt=100A/μs	-	32	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	39	-	nC

- Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature  
 2. EAS condition: T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>GS</sub>=10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=2.5A  
 3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

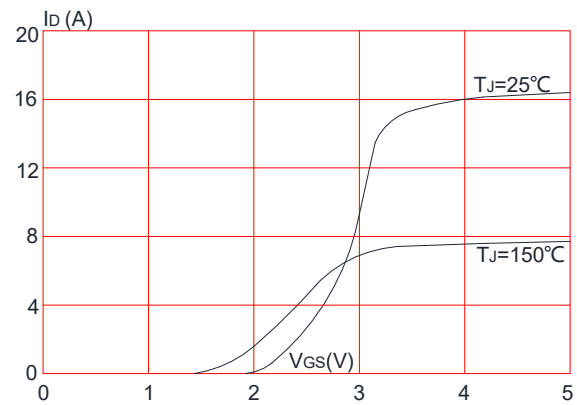


## Typical Performance Characteristics

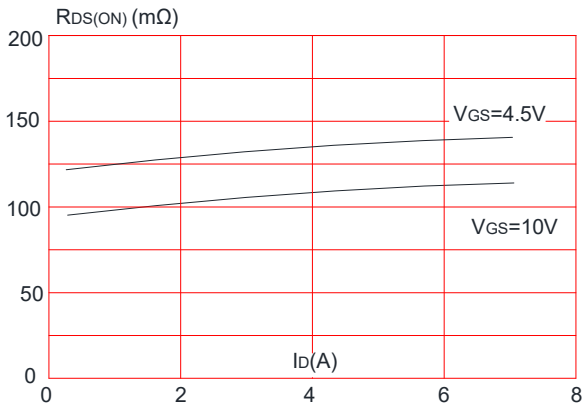
**Figure 1: Output Characteristics**



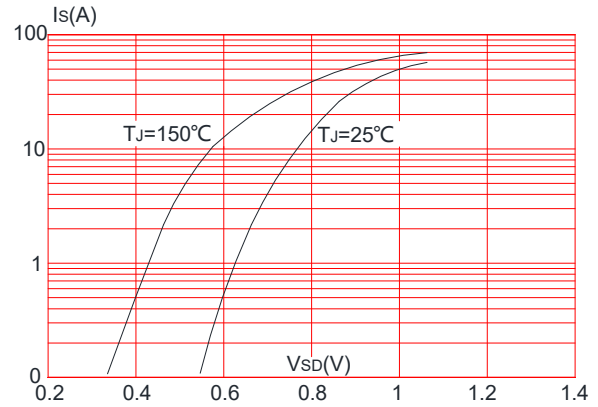
**Figure 2: Typical Transfer Characteristics**



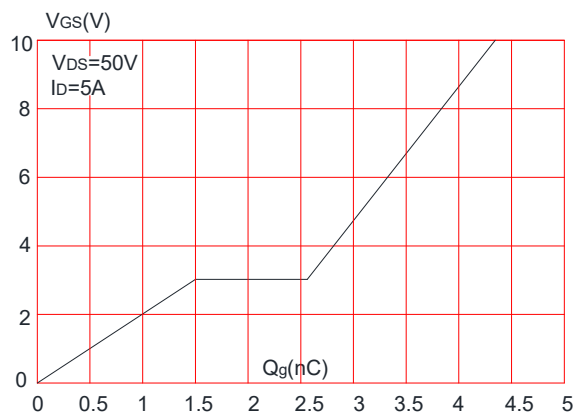
**Figure 3: On-resistance vs. Drain Current**



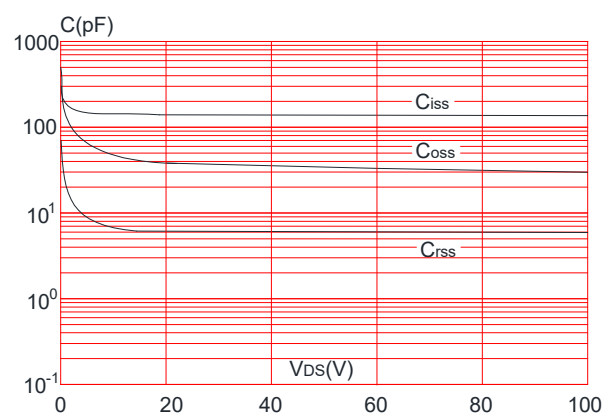
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

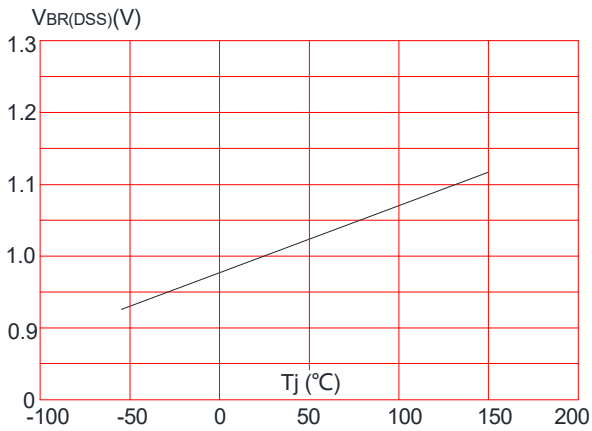


**Figure 6: Capacitance Characteristics**

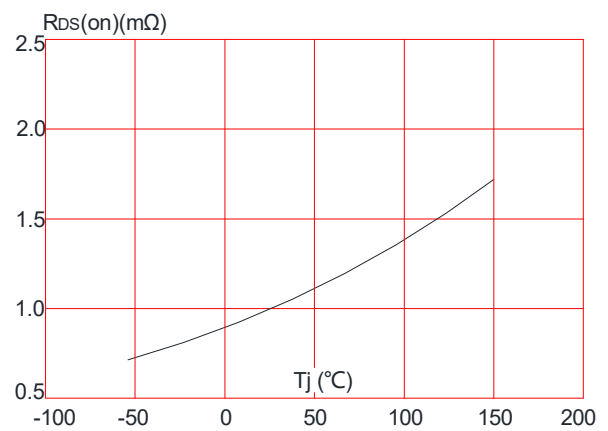




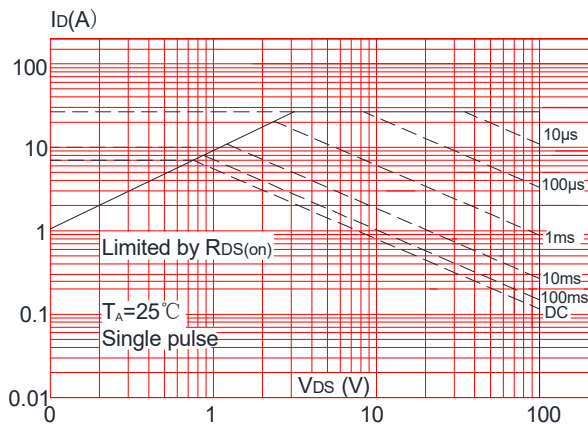
**Figure 7: Normalized Breakdown Voltage vs. Junction Temperature**



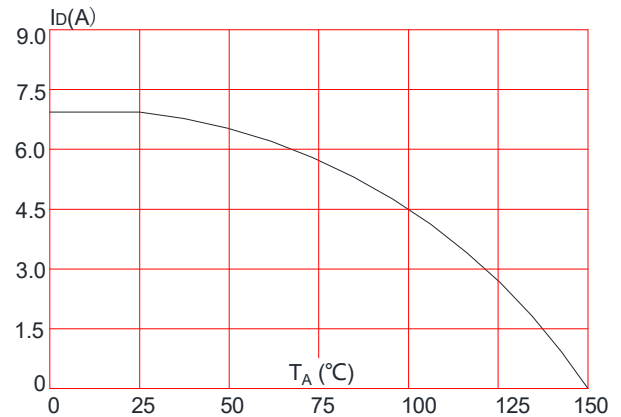
**Figure 8: Normalized on Resistance vs. Junction Temperature**



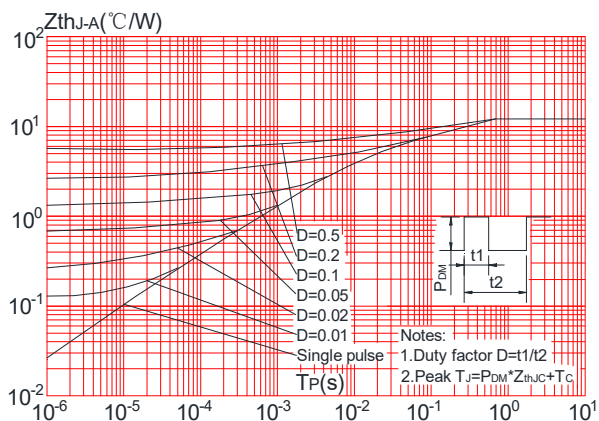
**Figure 9: Maximum Safe Operating Area**



**Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature**



**Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient**



## Test Circuit

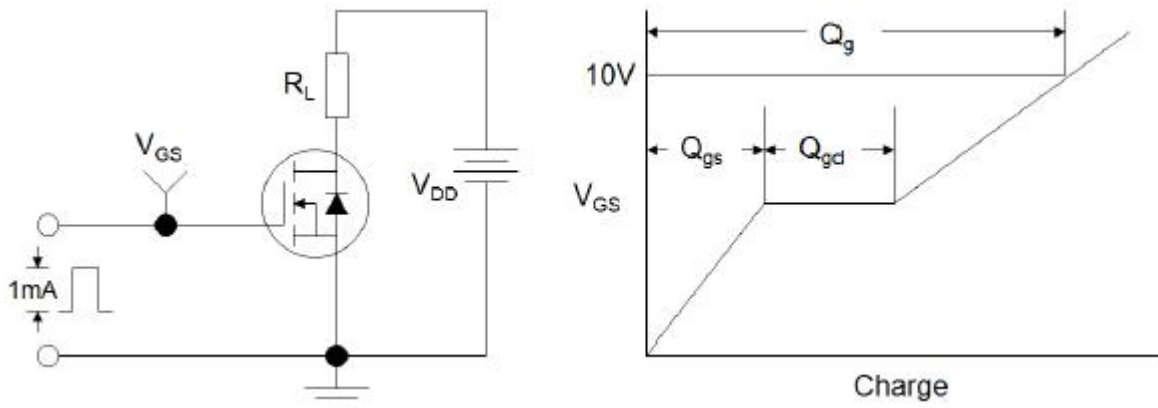


Figure1:Gate Charge Test Circuit & Waveform

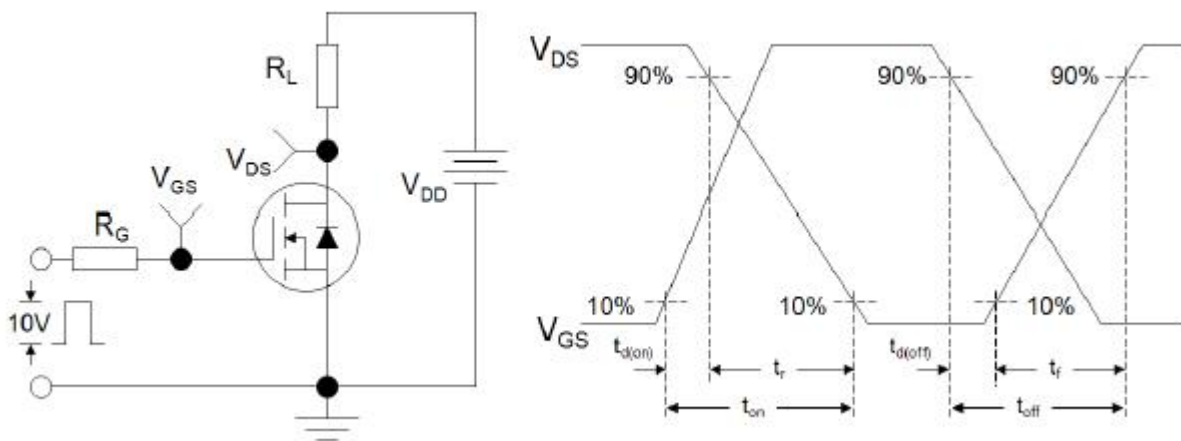


Figure 2: Resistive Switching Test Circuit & Waveforms

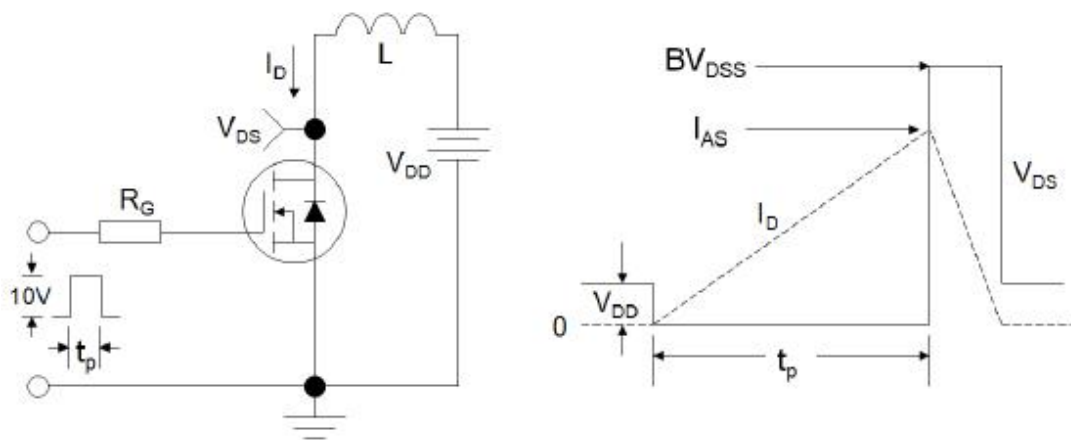
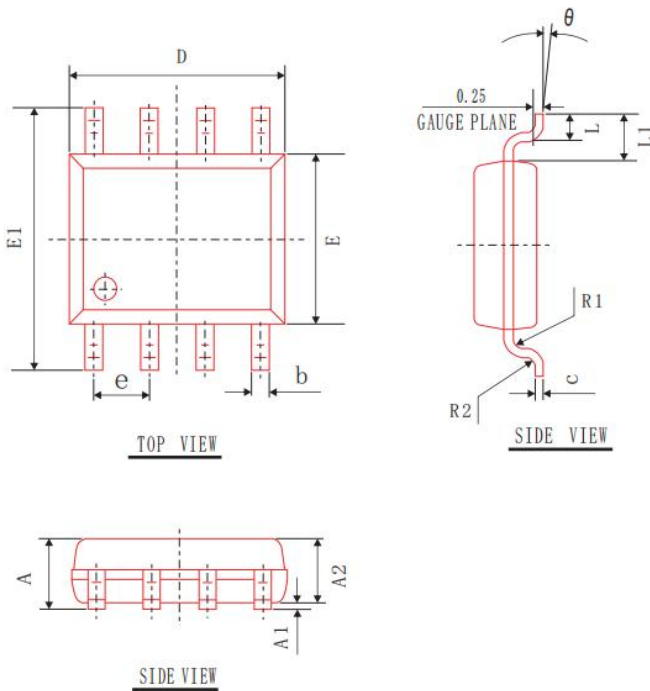


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



## Package Mechanical Data-SOP-8

COMMON DIMENSIONS  
(UNITS OF MEASURE=mm)




SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
$\theta$	2°	4°	6°
L 1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

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